

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (L<sup>2</sup>-π-MOSV)

# 2SK2745

Chopper Regulator, DC-DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance :  $R_{DS(ON)} = 7.0 \text{ m}\Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 50 \text{ S}$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 50 \text{ V}$ )
- Enhancement mode :  $V_{th} = 0.8 \text{ to } 2.0 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

## Absolute Maximum Ratings (Ta = 25°C)

| Characteristics                                      | Symbol         | Rating     | Unit |   |
|--|----------------|------------|------|---|
| Drain-source voltage                                 | $V_{DSS}$      | 50         | V    |   |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) | $V_{DGR}$      | 50         | V    |   |
| Gate-source voltage                                  | $V_{GSS}$      | $\pm 20$   | V    |   |
| Drain current  | DC (Note 1)    | $I_D$      | 50   | A |
|  | Pulse (Note 1) | $I_{DP}$   | 200  | A |
| Drain power dissipation ( $T_c = 25^\circ\text{C}$ ) | $P_D$          | 150        | W    |   |
| Single pulse avalanche energy (Note 2)               | $E_{AS}$       | 747        | mJ   |   |
| Avalanche current                                    | $I_{AR}$       | 50         | A    |   |
| Repetitive avalanche energy (Note 3)                 | $E_{AR}$       | 15         | mJ   |   |
| Channel temperature                                  | $T_{ch}$       | 150        | °C   |   |
| Storage temperature range                            | $T_{stg}$      | -55 to 150 | °C   |   |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Thermal Characteristics

| Characteristics                        | Symbol         | Max   | Unit   |
|--|----------------|-------|--------|
| Thermal resistance, channel to case    | $R_{th(ch-c)}$ | 0.833 | °C / W |
| Thermal resistance, channel to ambient | $R_{th(ch-a)}$ | 50    | °C / W |

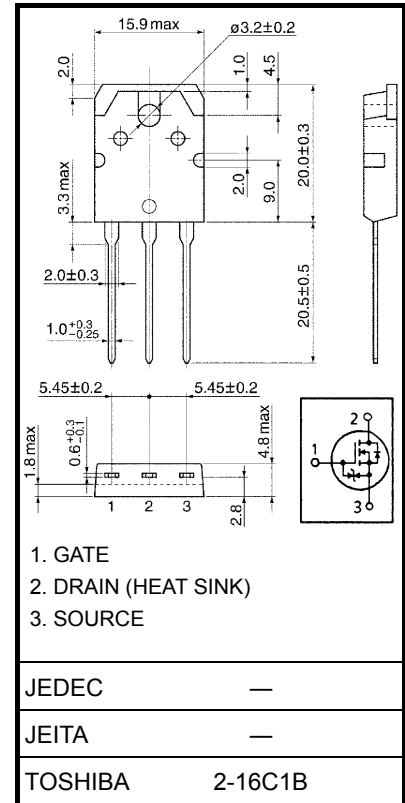
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 25 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 368 \text{ }\mu\text{H}$ ,  $R_G = 25 \text{ }\Omega$ ,  $I_{AR} = 50 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.  
Please handle with caution.

Unit: mm



Weight: 4.6 g (typ.)

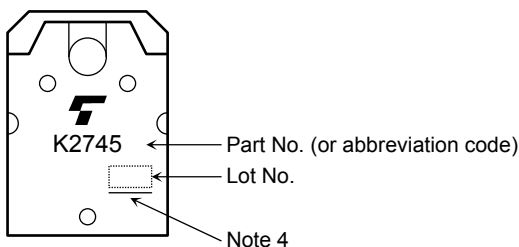
## Electrical Characteristics (Ta = 25°C)

| Characteristics                                 |               | Symbol        | Test Condition  | Min | Typ. | Max      | Unit          |
|---|---------------|---------------|---|-----|------|----------|---------------|
| Gate leakage current                            |               | $I_{GSS}$     | $V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$                       | —   | —    | $\pm 10$ | $\mu\text{A}$ |
| Drain cut-off current                           |               | $I_{DSS}$     | $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$                           | —   | —    | 100      | $\mu\text{A}$ |
| Drain-source breakdown voltage                  |               | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$                             | 50  | —    | —        | V             |
| Gate threshold voltage                          |               | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$                             | 0.8 | —    | 2.0      | V             |
| Drain-source ON resistance                      |               | $R_{DS(ON)}$  | $V_{GS} = 4\text{ V}, I_D = 25\text{ A}$                              | —   | 11   | 16       | m $\Omega$    |
|   |               |               | $V_{GS} = 10\text{ V}, I_D = 25\text{ A}$                             | —   | 7    | 9.5      |               |
| Forward transfer admittance                     |               | $ Y_{fs} $    | $V_{DS} = 10\text{ V}, I_D = 25\text{ A}$                             | 30  | 50   | —        | S             |
| Input capacitance                               |               | $C_{iss}$     | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$         | —   | 4000 | —        | pF            |
| Reverse transfer capacitance                    |               | $C_{rss}$     |   | —   | 800  | —        |               |
| Output capacitance                              |               | $C_{oss}$     |   | —   | 2000 | —        |               |
| Switching time                                  | Rise time     | $t_r$         |   | —   | 25   | —        | ns            |
|   | Turn-on time  | $t_{on}$      |   | —   | 40   | —        |               |
|   | Fall time     | $t_f$         |   | —   | 120  | —        |               |
|   | Turn-off time | $t_{off}$     |   | —   | 360  | —        |               |
| Total gate charge (gate-source plus gate-drain) |               | $Q_g$         | $V_{DD} \approx 40\text{ V}, V_{GS} = 10\text{ V}, I_D = 50\text{ A}$ | —   | 130  | —        | nC            |
| Gate-source charge                              |               | $Q_{gs}$      |   | —   | 90   | —        |               |
| Gate-drain ("miller") Charge                    |               | $Q_{gd}$      |   | —   | 40   | —        |               |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol    | Test Condition  | Min | Typ. | Max  | Unit          |
|---|-----------|---|-----|------|------|---------------|
| Continuous drain reverse current (Note 1) | $I_{DR}$  | —   | —   | —    | 50   | A             |
| Pulse drain reverse current (Note 1)      | $I_{DRP}$ | —   | —   | —    | 200  | A             |
| Forward voltage (diode)                   | $V_{DSF}$ | $I_{DR} = 50\text{ A}, V_{GS} = 0\text{ V}$   | —   | —    | -1.7 | V             |
| Reverse recovery time                     | $t_{rr}$  | $I_{DR} = 50\text{ A}, V_{GS} = 0\text{ V}, dI_{DR} / dt = 50\text{ A} / \mu\text{s}$ | —   | 140  | —    | ns            |
| Reverse recovery charge                   | $Q_{rr}$  |   | —   | 80   | —    | $\mu\text{C}$ |

## Marking

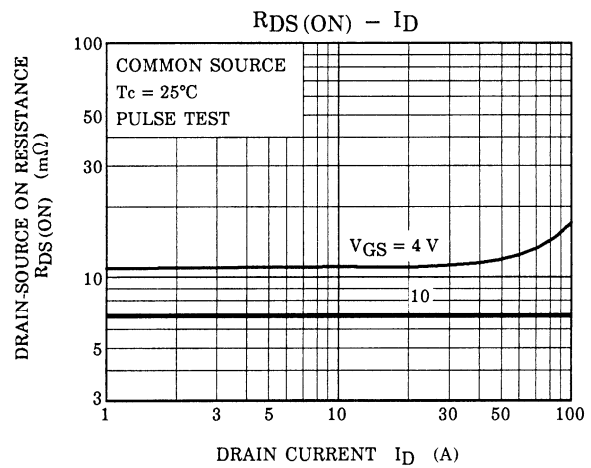
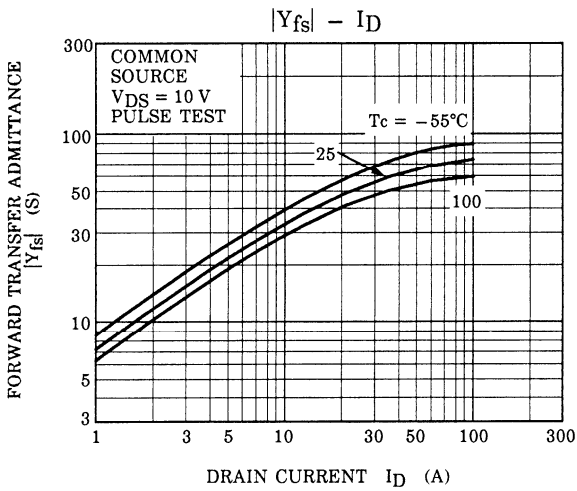
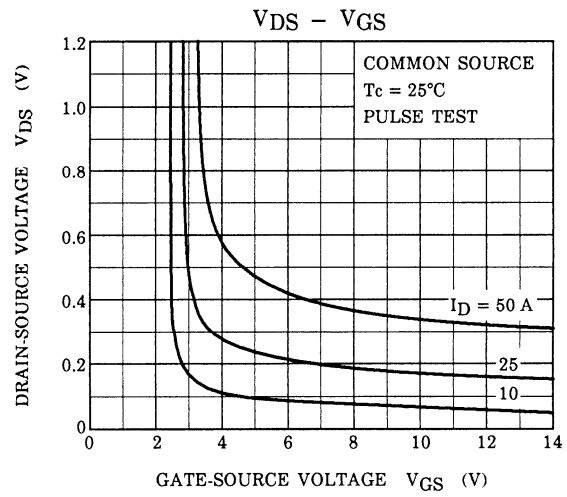
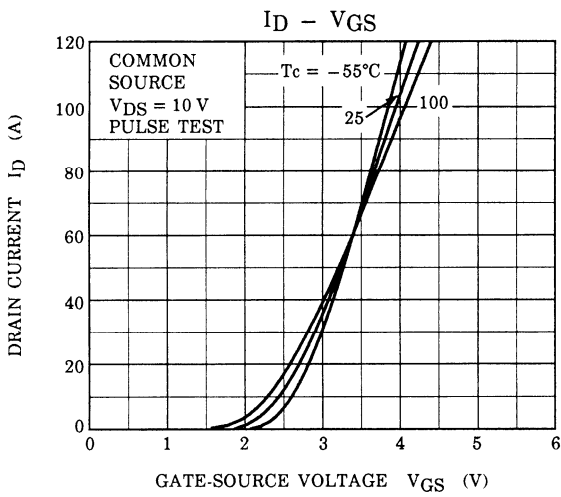
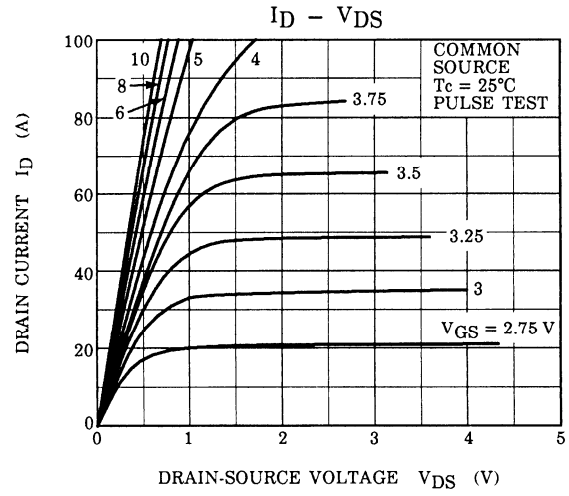
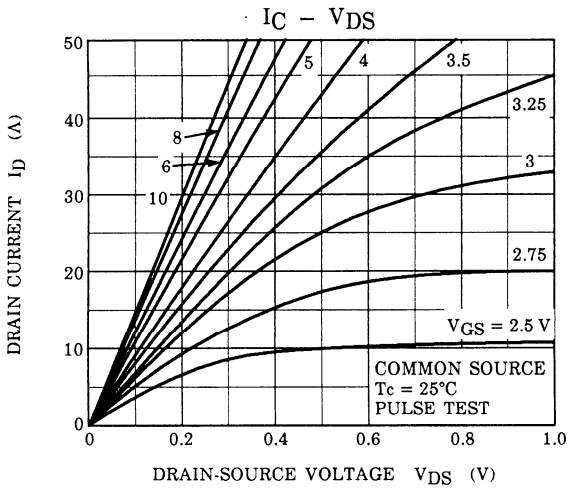


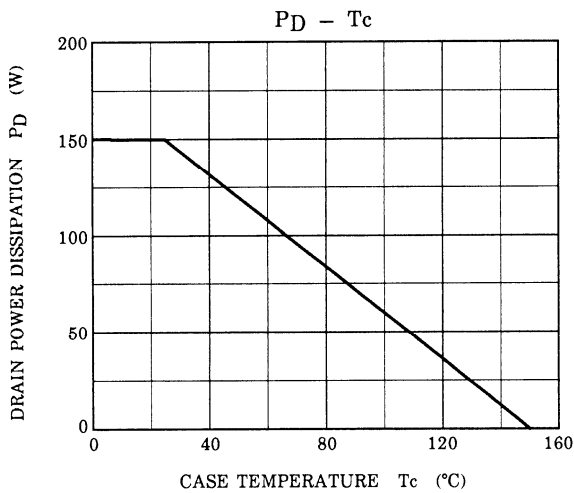
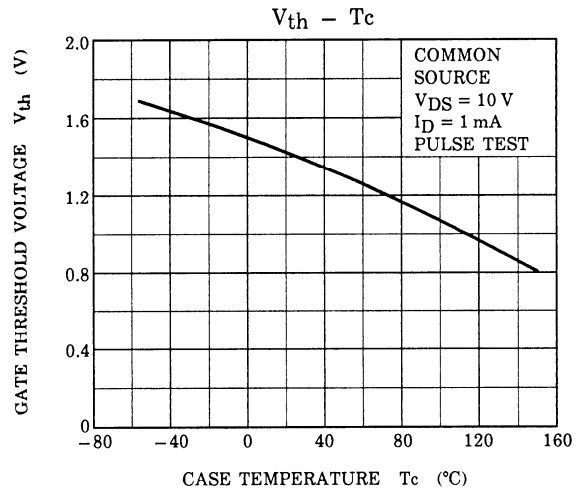
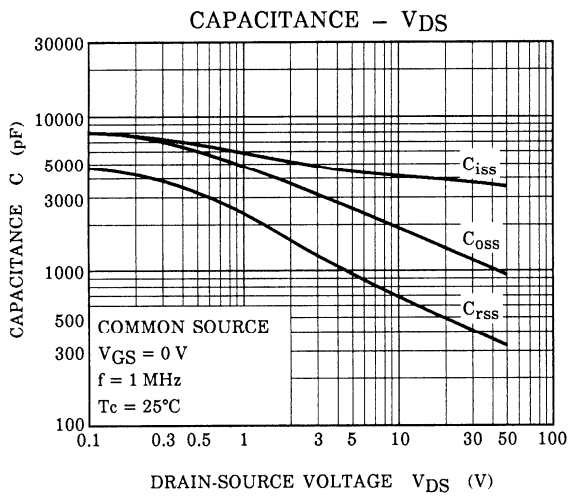
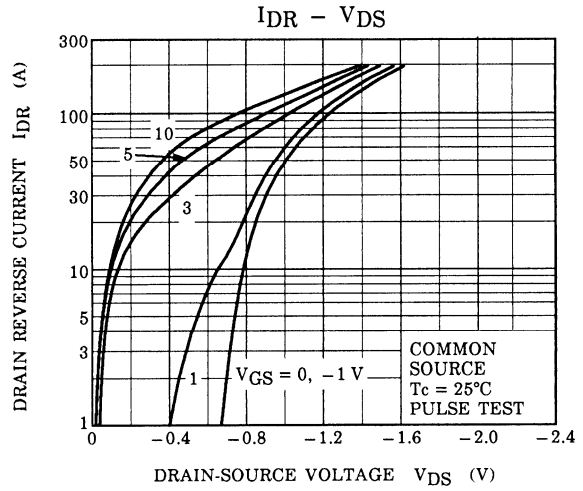
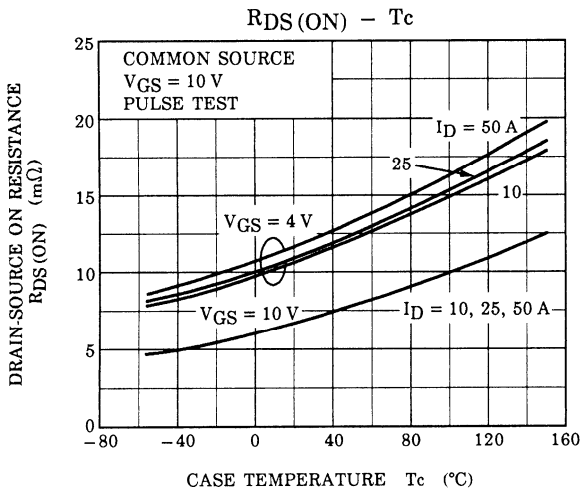
Note 4: A line under a Lot No. identifies the indication of product Labels.

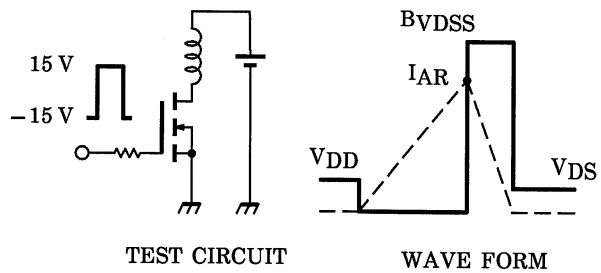
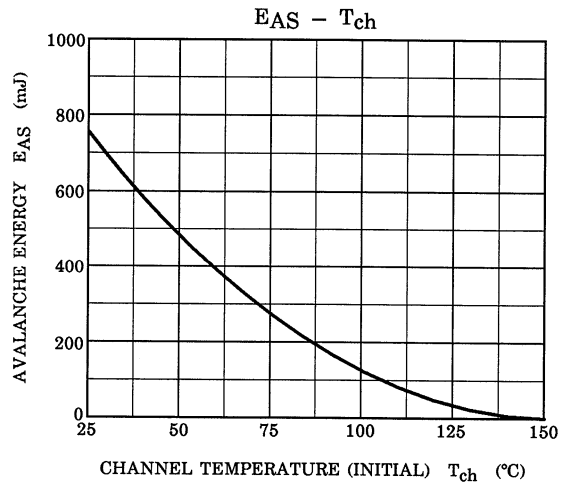
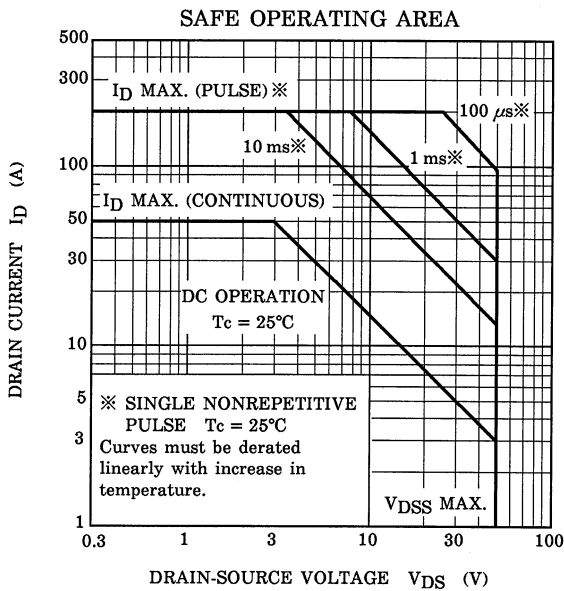
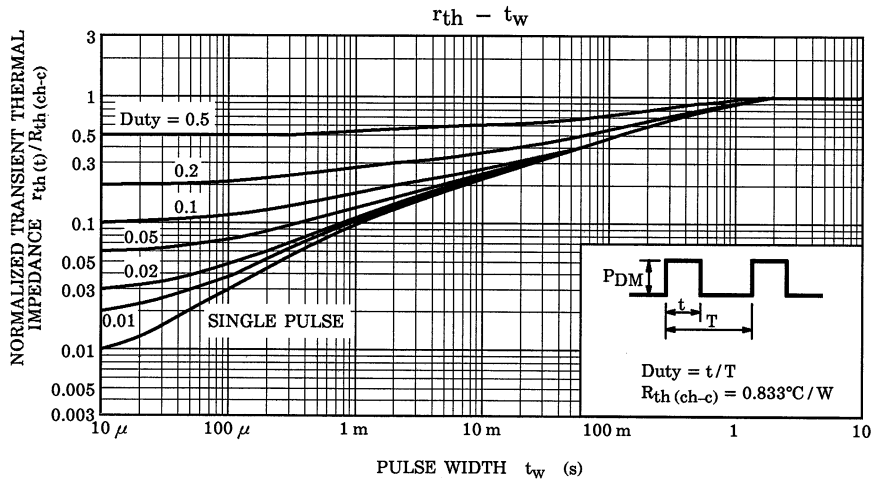
Not underlined:  $[[\text{Pb}]]/\text{INCLUDES} > \text{MCV}$

Underlined:  $[[\text{G}]]/\text{RoHS COMPATIBLE}$  or  $[[\text{G}]]/\text{RoHS} [[\text{Pb}]]$

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.







$R_G = 25 \Omega$   
 $V_{DD} = 25 V, L = 368 \mu H$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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